TOSHIBA TRANSISTOR SILICON-GERMANIUM NPN EPITAXIAL PLANER TYPE

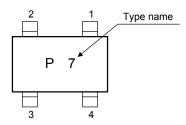
# MT4S101U

UHF LOW NOISE AMPLIFIER APPLICATION

### FEATURES

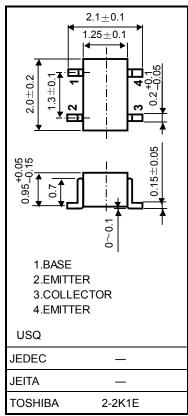
- Low Noise Figure :NF=0.8dB (@f=2GHz)
- High Gain:|S21e|<sup>2</sup>=16.0dB (@f=2GHz)

### Marking



#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V <sub>CBO</sub>	6	V
Collector-Emitter voltage	V <sub>CEO</sub>	3	V
Emitter-Base voltage	V <sub>EBO</sub>	1.2	V
Collector-Current	IC	10	mA
Base-Current	Ι <sub>Β</sub>	5	mA
Collector Power dissipation	PC	30	mW
Junction temperature	Tj	150	°C
Storage temperature Range	T <sub>stg</sub>	-55~150	°C



Weight: 0.006 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

## **Microwave Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	fT	V <sub>CE</sub> =2V, I <sub>C</sub> =7mA, f=2GHz	17	21	-	GHz
Insertion Gain	S21e  <sup>2</sup>	V <sub>CE</sub> =2V, I <sub>C</sub> =7mA, f=2GHz	13.5	16	-	dB
Noise Figure	NF	V <sub>CE</sub> =2V, I <sub>C</sub> =5mA, f=2GHz	-	0.8	1.05	dB

### **Electrical Characteristics (Ta = 25°C)**

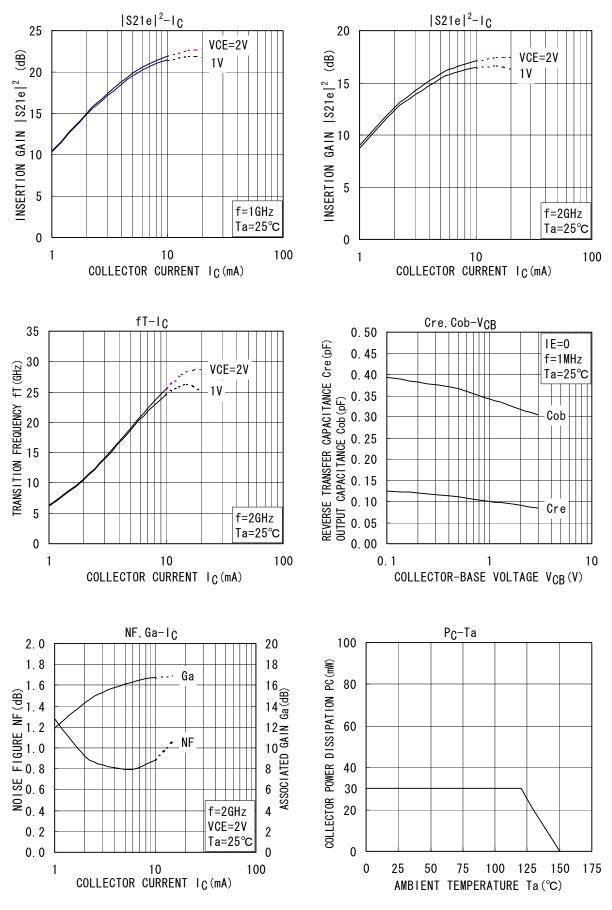
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =6V, I <sub>E</sub> =0	-	-	1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =1V, I <sub>C</sub> =0	-	-	1	μA
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =7mA	200	-	400	-
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz	-	0.34	0.6	pF
Reverse Transistor Capacitance	C <sub>re</sub>	V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz (Note 1)	-	0.1	0.2	pF

**Note 1:** Cre is measured by 3 terminal method with capacitance bridge.

**Caution:** This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

# TOSHIBA



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20070701-EN GENERAL

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